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BaNbO(IO₃)₅: A New Polar Material with a Very Large SHG Response

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The search for new second-order nonlinear optical (NLO) materials is of current interest and great importance because of their applications in photonic technologies.¹ Currently, the most widely used such materials are inorganic crystals based on borates [such as β -BaB₂O₄ (BBO) and LiB₃O₅ (LBO)] and phosphates [such as KH₂PO₄ (KDP) and KTiOPO4 (KTP)].^{2,3} Metal borophosphates containing both borate and phosphate groups are also promising NLO materials.⁴ Recently, we found that a combination of B-O bonds and lone-pair-containing Se(IV) cations, which are susceptible to second-order Jahn-Teller (SOJT) distortion, can also afford a new type of second-order NLO compound.⁵ It has been reported that the combination of transitionmetal ions having a d⁰ electronic configuration, such as W⁶⁺ or Mo⁶⁺, and lone-pair-containing Se(IV) or Te(IV) cations, both susceptible to SOJT distortions, can also form inorganic solids with excellent SHG properties as a result of the "additive" polarizations of the two types of bonds.⁶ Metal iodates such as α-LiIO₃, which also contain a lonepair cation, I5+, in an asymmetric coordination geometry, have been reported to show a wide transparency region, large second-harmonic generation (SHG) coefficients, high optical-damage thresholds, and good thermal stability.^{7,8} As for metal selenites and tellurites, d⁰ transition-metal ions such as Ti⁴⁺, V⁵⁺, W⁶⁺, and Mo⁶⁺ have been introduced into metal iodate systems to aid in the formation of noncentrosymmetric (NCS) structures and enhance their SHG properties.^{9,10} To the best of our knowledge, no metal iodates with added Nb⁵⁺ cations have been reported to date. The NbO₆ octahedron, which is usually moderately distorted toward a corner (the local C_4 direction),¹¹ may favor alignment with the asymmetric iodate groups in such a way that the two types of polarization lie along the same direction, thereby producing polar materials with a very large SHG response. Guided by this idea, we successfully obtained a new polar material, BaNbO(IO₃)₅, with a very large SHG response (\sim 14 times that of KDP and ~660 times that of α -SiO₂). Herein we report its synthesis, crystal structure, and ferroelectric and NLO properties.

BaNbO(IO₃)₅ was synthesized as a single phase in 83% yield (based on Ba) by the hydrothermal reaction of Ba(IO₃)₂•H₂O (1.0 mmol), Nb₂O₅ (0.6 mmol), and I₂O₅ (9 mmol) in 5 mL of water sealed in an autoclave equipped with a Teflon liner (23 mL) at 230 °C for 4 days (see the Supporting Information). The presence of a unique phase was confirmed by powder X-ray diffraction (XRD) (Figure S1). The Ba/ Nb/I molar ratio measured by microprobe energy-dispersive spectroscopy analysis was 1.1:1.3:6.0, which is close to that determined from single-crystal XRD analysis.¹² BaNbO(IO₃)₅ crystallizes in the acentric space group *Cc* (No. 9). Its anionic structure may be considered to be "zero-dimensional" (0D) and is composed of a NbO₆ octahedron linked with five IO₃⁻ groups and one terminal O²⁻ anion, with the Ba²⁺ cations acting as spacers between these anions (Figure 1 and Figure S3). Both the Nb⁵⁺ and I⁵⁺ cations are in asymmetric coordination

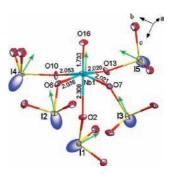


Figure 1. ORTEP drawing (with 50% probability ellipsoids) showing the "zero-dimensional" $[NbO(IO_3)_5]^{2-}$ anion, lone pairs (blue ellipsoids), and local moments (green arrows) in BaNbO(IO₃)₅.

environments attributed to SOJT effects. The Nb5+ cation undergoes intraoctahedral distortion toward the terminal oxide ligand, that is, a corner ($C_4[001]$) distortion (see Figure 1), resulting in one "short" [1.733(7) Å], one "long" [2.308(8) Å], and four "normal" [2.020(8)-2.053(8) Å] Nb⁵⁺-O bonds. The magnitude of the out-of-center distortion (Δd) was estimated to be 0.63.¹¹ All five I⁵⁺ cations are in distorted trigonal-pyramidal environments, being coordinated by three oxygen atoms. The I-O distances range from 1.780(9) to 1.899(7) Å, comparable to those reported in other metal iodates.^{7,8} It should be mentioned that the above 0D anionic units are further interconnected by weak I1–O4 bonds with lengths of 2.452(9) Å into a chain along the *a* axis (Figure S3b). The Ba^{2+} ion is surrounded by 10 oxygen atoms, one from a terminal O²⁻ anion and nine from IO₃ groups in a unidentate fashion, with Ba-O distances in the range 2.623(7)-3.162(9) Å. The results of bond valence calculations (Ba, 2.28; Nb, 4.84; I, 4.86-5.01) indicate that the Ba, Nb, and I atoms are in oxidation states of +2, +5, and +5 respectively.¹³

The IR spectrum of BaNbO(IO₃)₅ shows the characteristic absorption bands of ν_{Nb-O} (924 cm⁻¹) and ν_{I-O} (478–833 cm⁻¹) (Figure S4).^{9,14} Its UV absorption spectrum reveals little absorption from 0.35 to 2.5 μ m (Figure S5). The optical diffuse reflectance spectrum indicates an optical band gap of 3.64 eV (Figure S6), and hence, BaNbO(IO₃)₅ is a wide-band-gap semiconductor. The thermogravimetric analysis (TGA) curve (Figure S7) shows that BaNbO(IO₃)₅ is stable up to 420 °C but then continually loses weight up to 700 °C. The sharp weight loss corresponds to the decomposition of the compound through thermal disproportionation, which releases 2.5 molecules of I₂ and 6.25 molecules of O₂.^{9,10} The total weight loss of 73.8% at 700 °C was close to the calculated value of 74.5%. The differential scanning calorimetry (DSC) diagram of BaNbO(IO₃)₅ exhibits two endothermic peaks at 456 and 593 °C, indicating that the compound melts incongruently.

The acentric structure of BaNbO(IO_3)₅ prompted us to measure its SHG properties. SHG measurements on sieved powder samples (80–100 mesh) using 1064 nm radiation¹⁵ revealed that BaNbO(IO_3)₅

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Figure 2. Calculated frequency-dependent SHG coefficients of BaNbO- $(IO_3)_{5}$

exhibits a very large SHG response, ~ 14 times that of KDP and ~ 660 times that of α -SiO₂. Furthermore, the compound was found to be phase-matchable (Figure S8). The extremely large SHG efficiency can be attributed to the synergistic effect of the polarizations of the asymmetric NbO₆ octahedra and the IO_3^- anions (Figure 1).

Piezoelectric measurements in a random direction on a single crystal with a size of $0.6 \times 1.0 \times 2.0 \text{ mm}^3$ gave a p_{33} value of ~8.1 pC/N, which is much smaller than that of $Li_2Ti(IO_3)_6$.^{10a} Ferroelectric measurements revealed a small maximum spontaneous polarization of 0.414 μ C/cm² (Figure S9). Hence, the coefficients are very small, and the ferroelectric properties are negligible.^{9,10} It is unlikely that the dipole moments associated with the asymmetric IO₃ polyhedra are reversible.^{9,10} Thus, the polarization reversibility is limited to the small contribution from the Nb⁵⁺ cation.

To gain further insights into the band structure and optical properties of BaNbO(IO₃)₅, theoretical calculations based on density functional theory (DFT) were performed using the total-energy code CASTEP.¹⁶

The results of band structure calculations (Figure S10) indicate that BaNbO(IO₃)₅ is a direct-gap semiconductor with a band gap of 2.55 eV, which is significantly smaller than the experimental value as a result of the limitations of DFT methods. The bands just above the Fermi level are predominately derived from Nb 4d, I 5p, and some O 2p states, whereas the band just below the Fermi level is composed of O 2p, I 5p, and Nb 4d states that mix with small amounts of I 5s states (Figure S11).

The linear optical response properties of BaNbO(IO₃)₅ were examined through calculation of the complex dielectric function $\varepsilon(\omega)$ = $\varepsilon_1(\omega)$ + $i\varepsilon_2(\omega)$. The imaginary part [$\varepsilon_2(\omega)$] of the frequencydependent dielectric function of BaNbO(IO₃)₅ shows anisotropy along different dielectric axis directions (Figure S12a). The curves of the average imaginary and real parts of the dielectric function were obtained as $\varepsilon_{ave} = (\varepsilon_x + \varepsilon_y + \varepsilon_z)/3$ (Figure S12b). The average imaginary part reveals the strongest adsorption peak at \sim 5.71 eV, which can be mainly assigned to electronic interband transitions from the O 2p state to I 5p and Nb 4d states. The average static dielectric constant is $\varepsilon(0) = 4.50$. The dispersion of the refractive index, which was calculated using the formula $n^2(\omega) = \varepsilon(\omega)$, indicates an order of $n^{z} > n^{y} > n^{x}$ (Figure S13). The values of n^{x} , n^{y} , and n^{z} at 1064 nm were calculated to be 2.128, 2.157, and 2.163, respectively.

The space group of BaNbO(IO₃)₅ belongs to class m and has 10 nonvanishing tensors of second-order susceptibility. Under the restriction of Kleinman's symmetry, only six independent SHG tensor components $(d_{11}, d_{12}, d_{13}, d_{15}, d_{24}, and d_{33})$ remain. The frequencydependent SHG tensor components of BaNbO(IO3)5 ars plotted in Figure 2. The values of d_{11} , d_{12} , d_{13} , d_{15} , d_{24} , and d_{33} at a wavelength of 1064 nm (1.165 eV) for BaNbO(IO₃)₅ are 1.98×10^{-8} , 2.12×10^{-8} 10^{-8} , 2.15×10^{-8} , 2.06×10^{-8} , 2.24×10^{-8} , and 2.26×10^{-8} esu, respectively. These values are close to our experimental value, which is 14 times that of KDP ($d_{36} = 1.1 \times 10^{-9}$ esu).

In summary, by the combination of the Nb⁵⁺ cation, which has a d⁰ electronic configuration, and the lone-pair-containing iodate anion, a new SHG material, BaNbO(IO₃)₅ has been prepared. It represents the first compound in the Ae/A-Nb⁵⁺-I⁵⁺-O system (Ae = alkaline-earth; A = alkali). It exhibits a very large SHG signal (\sim 14 times that of KDP) and is phase-matchable. It has also high thermal stability and a wide transparent region. On the basis of these arguments, it is concluded that this compound is potentially a new candidate for second-order NLO materials. Currently we are exploring other compounds in the Ae/A-Nb⁵⁺-I⁵⁺-O system and trying to grow larger-sized BaNbO(IO₃)₅ crystals in order to further study its optical properties.

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Supporting Information Available: Details of crystallographic studies (CIF), physical property measurements, and theoretical calculations for BaNbO(IO₃)₅. This material is available free of charge via the Internet at http://pubs.acs.org.

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